

TO-247 Plastic-Encapsulate Transistors

2SA1633 TRANSISTOR (PNP)

FEATURES

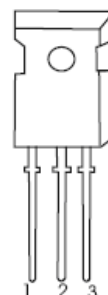
- High Breakdown Voltage
- High Current and High Power Capability

APPLICATIONS

- For Audio Output Applications

TO – 247

1. BASE
2. COLLECTOR
3. EMITTER



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-150	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-10	A
P _C	Collector Power Dissipation	3.5	W
R _{θJA}	Thermal Resistance From Junction To Ambient	36	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-150			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-50mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-10	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1A	60		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-5A, I _B =-0.5A			-2.5	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-1A	10			MHz



B, Nov, 2014